

2.5V Drive Nch+Nch MOSFET

US6K1

Structure

Silicon N-channel MOSFET

Features

- 1) Low On-resistance.
- 2) Space savingsmall surface mount package (TUMT6).
- 3) Low voltage drive (2.5V drive).

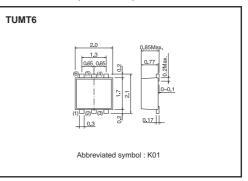
Applications

Switching

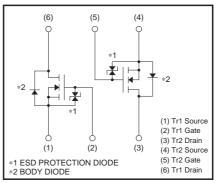
Packaging specifications

	Package	Taping
Туре	Code	TR
	Basic ordering unit (pieces)	3000
US6K1		0

•Dimensions (Unit : mm)



Inner circuit



•Absolute maximum ratings (Ta=25°C)

	0	,		
Parameter		Symbol	Limits	Unit
Drain-source voltage		V _{DSS}	30	V
Gate-source voltage		V _{GSS}	12	V
Desire comment	Continuous	ID	±1.5	A
Drain current	Pulsed	IDP *1	±6	А
Source current	Continuous	ls	0.6	А
(Body diode)	Pulsed	I _{SP} *1	6	А
Total power dissipation		Pd *2	1.0	W / TOTAL
		ΙD	0.7	W / ELEMENT
Channel temperature		Tch	150	٥C
Range of storage temperature		Tstg	-55 to +150	٥C
1 D 110 D 1 1 110/				

∗1 Pw≤10µs, Duty cycle≤1%

*2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W / TOTAL
	Rtif(cfi-a)	179	°C/W / ELEMENT

* Mounted on a ceramic board

•Electrical characteristics (Ta=25°C)

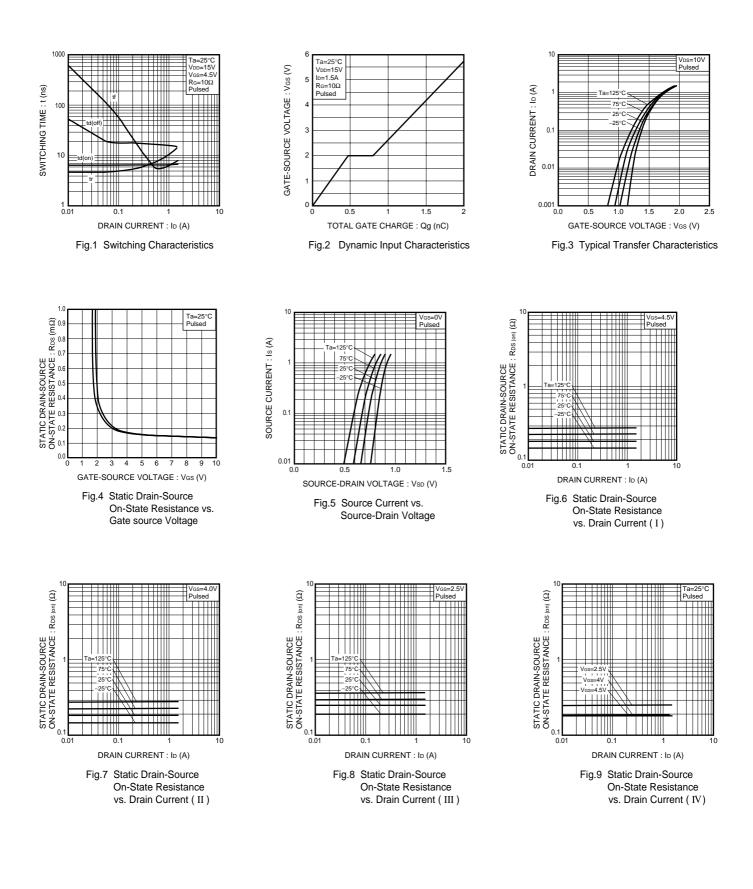
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	-	-	10	μΑ	V _{GS} =12V, V _{DS} =0V	
Drain-source breakdown voltage	V(BR) DSS	30	_	_	V	I _D = 1mA, V _{GS} =0V	
Zero gate voltage drain current	IDSS	_	_	1	μΑ	V _{DS} = 30V, V _{GS} =0V	
Gate threshold voltage	V _{GS (th)}	0.5	_	1.5	V	V _{DS} = 10V, I _D = 1mA	
Static drain-source on-state resistance	R _{DS} (on)*	-	170	240	mΩ	I _D = 1.5A, V _{GS} = 4.5V	
		-	180	250	mΩ	I _D = 1.5A, V _{GS} = 4.0V	
		-	240	340	mΩ	I _D = 1.5A, V _{GS} = 2.5V	
Forward transfer admittance	Y _{fs} *	1.5	_	_	S	V _{DS} = 10V, I _D = 1.5A	
Input capacitance	Ciss	-	80	_	pF	VDS= 10V	
Output capacitance	Coss	-	13	_	pF	V _{GS} =0V	
Reverse transfer capacitance	Crss	-	12	_	pF	f=1MHz	
Turn-on delay time	td (on) *	-	7	_	ns	Vdd≒ 15V	
Rise time	tr *	-	9	_	ns	$I_{D}=0.75A$	
Turn-off delay time	td (off) *	_	15	_	ns	Vgs= 4.5V R∟= 20Ω	
Fall time	t _f *	-	6	-	ns	$R_G = 10\Omega$	
Total gate charge	Qg *	-	1.6	2.2	nC	V _{DD} ≒15V	
Gate-source charge	Qgs *	-	0.5	-	nC	Vgs= 4.5V	
Gate-drain charge	Q _{gd} *	_	0.3	_	nC	I _D = 1.5A	

*Pulsed

•Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Forward voltage	Vsd	-	-	1.2	V	Is= 0.6A, V _{GS} =0V	

•Electrical characteristics curves



Notes

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